P-Type Amorphous Oxide Semiconductor Atomic Layer Deposition System

Deposition Process Library

- Al_2O_3
- HfO_2
- SnOx (x=1~2)* *: still under R&D stage

Thickness

- 10Å ~ 200Å

Process parameters

- Film: Al_2O_3
- Precursor: TMA
- Oxygen source: H_2O
- Pressure(hPa): 5~10
- Carrier gas: N_2
- Purge gas: N_2
- Temperature (℃): 250 ℃
- Substrate size: 6, 8 inch, chip

- Film: HfO_2
- Precursor: TMAHf
- Oxygen source: H_2O
- Pressure(hPa): 5~10
- Carrier gas: N_2
- Purge gas: N_2
- Temperature (℃): 250 ℃
- Substrate size: 6, 8 inch, chip

- Film: SnO_X
- Precursor: Sn precursor
- Oxygen source: H_2O
- Pressure(hPa): 5~10
- Carrier gas: N_2
- Purge gas: N_2
- Temperature (℃): 200 ℃
- Substrate size: 6, 8 inch, chip